

Joan M Redwing

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

278 papers	10,164 citations	56 h-index	90 g-index
306 ext. papers	11,331 ext. citations	5.2 avg, IF	6.01 L-index

#	Paper	IF	Citations
278	Atomic-scale probing of defect-assisted Ga intercalation through graphene using ReaxFF molecular dynamics simulations. <i>Carbon</i> , 2022 , 190, 276-290	10.4	3
277	Realization of electronic-grade two-dimensional transition metal dichalcogenides by thin-film deposition techniques 2022 , 159-193		
276	Low-temperature processed beta-phase In ₂ Se ₃ ferroelectric semiconductor thin film transistors. <i>2D Materials</i> , 2022 , 9, 025023	5.9	2
275	Light-matter coupling in large-area van der Waals superlattices. <i>Nature Nanotechnology</i> , 2021 ,	28.7	11
274	Substrate Modification during Chemical Vapor Deposition of hBN on Sapphire. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 54516-54526	9.5	3
273	Formation of metal vacancy arrays in coalesced WS ₂ monolayer films. <i>2D Materials</i> , 2021 , 8, 011003	5.9	7
272	Monolayer MoS ₂ on sapphire: an azimuthal reflection high-energy electron diffraction perspective. <i>2D Materials</i> , 2021 , 8, 025003	5.9	11
271	Interface Transparency and Rashba Spin Torque Enhancement in WSe Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 13744-13750	9.5	8
270	Hexagonal Boron Nitride Crystal Growth from Iron, a Single Component Flux. <i>ACS Nano</i> , 2021 , 15, 7032-7039	10.9	11
269	Influence of the Underlying Substrate on the Physical Vapor Deposition of Zn-Phthalocyanine on Graphene. <i>ACS Omega</i> , 2021 , 6, 20598-20610	3.9	0
268	S/TEM Characterization of Vertical Heterostructures Formed by Mono- to Multi-layer Graphene and WSe ₂ . <i>Microscopy and Microanalysis</i> , 2021 , 27, 894-895	0.5	0
267	Illuminating Invisible Grain Boundaries in Coalesced Single-Orientation WS Monolayer Films. <i>Nano Letters</i> , 2021 , 21, 6487-6495	11.5	7
266	Benchmarking monolayer MoS and WS field-effect transistors. <i>Nature Communications</i> , 2021 , 12, 693	17.4	66
265	Controllable p-Type Doping of 2D WSe ₂ via Vanadium Substitution. <i>Advanced Functional Materials</i> , 2021 , 31, 2105252	15.6	4
264	A ReaxFF Force Field for 2D-WS ₂ and Its Interaction with Sapphire. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 17950-17961	3.8	3
263	Theoretical modeling of edge-controlled growth kinetics and structural engineering of 2D-MoSe ₂ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021 , 271, 115263	3.1	3
262	Orientation domain dispersions in wafer scale epitaxial monolayer WSe ₂ on sapphire. <i>Applied Surface Science</i> , 2021 , 567, 150798	6.7	1

261	Wafer-Scale Epitaxial Growth of Unidirectional WS Monolayers on Sapphire. <i>ACS Nano</i> , 2021 , 15, 2532-2541	16.7	51
260	Gas source chemical vapor deposition of hexagonal boron nitride on C-plane sapphire using B ₂ H ₆ and NH ₃ . <i>Journal of Materials Research</i> , 2021 , 36, 4678-4687	2.5	3
259	Spin-dependent vibronic response of a carbon radical ion in two-dimensional WS ₂ . <i>Nature Communications</i> , 2021 , 12, 7287	17.4	2
258	Modeling for Structural Engineering and Synthesis of Two-Dimensional WSe ₂ Using a Newly Developed ReaxFF Reactive Force Field. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 28285-28297	3.8	10
257	Cathodoluminescence spatially resolves optical transitions in thick group-III and N-polar InGa _N films. <i>Journal of Applied Physics</i> , 2020 , 128, 175305	2.5	
256	Scalable Substitutional Re-Doping and its Impact on the Optical and Electronic Properties of Tungsten Diselenide. <i>Advanced Materials</i> , 2020 , 32, e2005159	24	11
255	Epitaxial Growth of Two-Dimensional Layered Transition Metal Dichalcogenides. <i>Annual Review of Materials Research</i> , 2020 , 50, 155-177	12.8	27
254	Hexagonal Boron Nitride Single Crystal Growth from Solution with a Temperature Gradient. <i>Chemistry of Materials</i> , 2020 , 32, 5066-5072	9.6	8
253	Fundamental limitations in transferred CVD graphene caused by Cu catalyst surface morphology. <i>Carbon</i> , 2020 , 163, 95-104	10.4	24
252	Enhancement of WSe ₂ FET Performance Using Low-Temperature Annealing. <i>Journal of Electronic Materials</i> , 2020 , 49, 3770-3779	1.9	3
251	Temperature-Dependent RF Characteristics of Al ₂ O ₃ -Passivated WSe ₂ MOSFETs. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1134-1137	4.4	
250	Interdependence of Electronic and Thermal Transport in Al _x Ga _{1-x} N Channel HEMTs. <i>IEEE Electron Device Letters</i> , 2020 , 41, 461-464	4.4	11
249	Van der Waals epitaxy and composition control of layered Sn _x Se _{2-x} alloy thin films. <i>Journal of Materials Research</i> , 2020 , 35, 1386-1396	2.5	0
248	Scalable low-temperature synthesis of two-dimensional materials beyond graphene. <i>JPhys Materials</i> , 2020 , 4, 012001	4.2	10
247	Defect creation in WSe ₂ with a microsecond photoluminescence lifetime by focused ion beam irradiation. <i>Nanoscale</i> , 2020 , 12, 2047-2056	7.7	13
246	Epitaxial growth of few-layer E _n Se ₃ thin films by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2020 , 533, 125471	1.6	8
245	Scalable BEOL compatible 2D tungsten diselenide. <i>2D Materials</i> , 2020 , 7, 015029	5.9	25
244	Single- versus Dual-Ion Conductors for Electric Double Layer Gating: Finite Element Modeling and Hall-Effect Measurements. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 40850-40858	9.5	2

243	Stochastic resonance in MoS photodetector. <i>Nature Communications</i> , 2020 , 11, 4406	17.4	30
242	A low-power biomimetic collision detector based on an in-memory molybdenum disulfide photodetector. <i>Nature Electronics</i> , 2020 , 3, 646-655	28.4	57
241	Locally defined quantum emission from epitaxial few-layer tungsten diselenide. <i>Applied Physics Letters</i> , 2019 , 114, 213102	3.4	9
240	Effect of Ge doping on growth stress and conductivity in Al _x Ga _{1-x} N. <i>Applied Physics Letters</i> , 2019 , 114, 142101	3.4	11
239	Atomic layer deposition of ZnO on MoS ₂ and WSe ₂ . <i>Applied Surface Science</i> , 2019 , 480, 43-51	6.7	16
238	GaN Heteroepitaxy on Strain-Engineered (111) Si/Si _{1-x} Ge _x . <i>Journal of Electronic Materials</i> , 2019 , 48, 3355-3362	1.9	0
237	Multi-wafer batch synthesis of graphene on Cu films by quasi-static flow chemical vapor deposition. <i>2D Materials</i> , 2019 , 6, 045032	5.9	10
236	Room-Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects. <i>Advanced Materials</i> , 2019 , 31, e1904132	24	34
235	Multidimensional thermal analysis of an ultrawide bandgap AlGa _N channel high electron mobility transistor. <i>Applied Physics Letters</i> , 2019 , 115, 153503	3.4	21
234	Multi-scale modeling of gas-phase reactions in metal-organic chemical vapor deposition growth of WSe ₂ . <i>Journal of Crystal Growth</i> , 2019 , 527, 125247	1.6	25
233	Defect-Controlled Nucleation and Orientation of WSe on hBN: A Route to Single-Crystal Epitaxial Monolayers. <i>ACS Nano</i> , 2019 , 13, 3341-3352	16.7	70
232	Chiral Metamaterials: Room-Temperature Active Modulation of Valley Dynamics in a Monolayer Semiconductor through Chiral Purcell Effects (Adv. Mater. 49/2019). <i>Advanced Materials</i> , 2019 , 31, 1970347	24	1
231	A roadmap for electronic grade 2D materials. <i>2D Materials</i> , 2019 , 6, 022001	5.9	133
230	Effect of substrate on the growth and properties of thin 3R NbS ₂ films grown by chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2018 , 486, 137-141	1.6	17
229	Diffusion-Controlled Epitaxy of Large Area Coalesced WSe Monolayers on Sapphire. <i>Nano Letters</i> , 2018 , 18, 1049-1056	11.5	136
228	Heteroepitaxy of Highly Oriented GaN Films on Non-Single Crystal Substrates Using a Si(111) Template Layer Formed by Aluminum-Induced Crystallization. <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1700392	2.5	3
227	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. <i>ACS Nano</i> , 2018 , 12, 965-975	16.7	127
226	Heteroepitaxy of Highly Oriented GaN Films on Non-Single Crystal Substrates Using a Si(111) Template Layer Formed by Aluminum-Induced Crystallization (Phys. Status Solidi RRL 3/2018). <i>Physica Status Solidi - Rapid Research Letters</i> , 2018 , 12, 1870311	2.5	

225	Understanding Interlayer Coupling in TMD-hBN Heterostructure by Raman Spectroscopy. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4059-4067	2.9	18
224	Chalcogen Precursor Effect on Cold-Wall Gas-Source Chemical Vapor Deposition Growth of WS ₂ . <i>Crystal Growth and Design</i> , 2018 , 18, 4357-4364	3.5	28
223	In-plane x-ray diffraction for characterization of monolayer and few-layer transition metal dichalcogenide films. <i>Nanotechnology</i> , 2018 , 29, 055706	3.4	19
222	Room Temperature Photonic Crystal Surface Emitting Laser with Synthesized Monolayer Tungsten Disulfide 2018 ,		1
221	Aluminum-Catalyzed Growth of Silicon Nanowires in High-Energy Growth Directions. <i>ACS Applied Nano Materials</i> , 2018 , 1, 5493-5499	5.6	1
220	Considerations for Utilizing Sodium Chloride in Epitaxial Molybdenum Disulfide. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 40831-40837	9.5	42
219	Atomic Structure of W _{1-x} Mo _x S ₂ Alloys and Heterostructures. <i>Microscopy and Microanalysis</i> , 2018 , 24, 1628-1629	0.5	
218	High Resolution S/TEM Study of Defects in MOCVD Grown Mono to Few Layer WS ₂ . <i>Microscopy and Microanalysis</i> , 2018 , 24, 1636-1637	0.5	
217	The effect of polarity on MOCVD growth of thick InGa _N . <i>Applied Physics Letters</i> , 2017 , 110, 022101	3.4	15
216	Controlled synthesis of 2D transition metal dichalcogenides: from vertical to planar MoS ₂ . <i>2D Materials</i> , 2017 , 4, 025029	5.9	48
215	Sulfidation of 2D transition metals (Mo, W, Re, Nb, Ta): thermodynamics, processing, and characterization. <i>Journal of Materials Science</i> , 2017 , 52, 10127-10139	4.3	13
214	Controlling silicon crystallization in aluminum-induced crystallization via substrate plasma treatment. <i>Journal of Applied Physics</i> , 2017 , 121, 115301	2.5	9
213	In situ stress measurements during MOCVD growth of thick N-polar InGa _N . <i>Journal of Applied Physics</i> , 2017 , 122, 085303	2.5	4
212	Uniform p-type doping of silicon nanowires synthesized via vapor-liquid-solid growth with silicon tetrachloride. <i>Journal of Applied Physics</i> , 2017 , 122, 235101	2.5	7
211	Two-dimensional gallium nitride realized via graphene encapsulation. <i>Nature Materials</i> , 2016 , 15, 1166-1171	11.7	447
210	Lateral Versus Vertical Growth of Two-Dimensional Layered Transition-Metal Dichalcogenides: Thermodynamic Insight into MoS ₂ . <i>Nano Letters</i> , 2016 , 16, 5742-50	11.5	70
209	Thin Film Transistors Using Wafer-Scale Low-Temperature MOCVD WSe ₂ . <i>Journal of Electronic Materials</i> , 2016 , 45, 6280-6284	1.9	18
208	Influence of Carbon in Metalorganic Chemical Vapor Deposition of Few-Layer WSe ₂ Thin Films. <i>Journal of Electronic Materials</i> , 2016 , 45, 6273-6279	1.9	35

207	Synthesis, characterization and chemical stability of silicon dichalcogenides, Si(SexS1-x)2. <i>Journal of Crystal Growth</i> , 2016 , 452, 151-157	1.6	10
206	Hybrid physical-chemical vapor deposition of Bi2Se3 films. <i>Journal of Crystal Growth</i> , 2016 , 452, 230-234	1.6	5
205	Silicon Micro/Nanowire Solar Cells. <i>Semiconductors and Semimetals</i> , 2016 , 94, 185-225	0.6	5
204	Carrier gas effects on aluminum-catalyzed nanowire growth. <i>Nanotechnology</i> , 2016 , 27, 135605	3.4	4
203	Study on Chemical Vapor Deposition Growth and Transmission electron Microscopy MoS2 /h-BN Heterostructure. <i>Microscopy and Microanalysis</i> , 2016 , 22, 1640-1641	0.5	2
202	Aluminum-catalyzed silicon nanowires: Growth methods, properties, and applications. <i>Applied Physics Reviews</i> , 2016 , 3, 040806	17.3	11
201	Heteroepitaxial growth of GaN on vertical Si{110} sidewalls formed on trench-etched Si(001) substrates. <i>Journal of Crystal Growth</i> , 2016 , 446, 1-6	1.6	3
200	Controlled faceting and morphology for light trapping in aluminum-catalyzed silicon nanostructures. <i>Journal of Crystal Growth</i> , 2016 , 452, 248-252	1.6	2
199	Radial Junction Silicon Nanowire Photovoltaics With Heterojunction With Intrinsic Thin Layer (HIT) Structure. <i>IEEE Journal of Photovoltaics</i> , 2016 , 6, 1446-1450	3.7	3
198	Aluminum-Catalyzed Growth of 110 Silicon Nanowires. <i>Journal of Electronic Materials</i> , 2015 , 44, 1332-1337	3.7	5
197	Magnetotransport phenomena in Bi2Se3 thin film topological insulators grown by hybrid physical chemical vapor deposition. <i>Journal of Applied Physics</i> , 2015 , 117, 065302	2.5	3
196	Vapor-Liquid-Solid Growth of Semiconductor Nanowires		7
195	In situ stress measurements during direct MOCVD growth of GaN on SiC. <i>Journal of Materials Research</i> , 2015 , 30, 2900-2909	2.5	5
194	The effects of shell layer morphology and processing on the electrical and photovoltaic properties of silicon nanowire radial p+ - n+ junctions. <i>Nanoscale</i> , 2015 , 7, 7267-74	7.7	3
193	The impact of graphene properties on GaN and AlN nucleation. <i>Surface Science</i> , 2015 , 634, 81-88	1.8	73
192	Highly scalable, atomically thin WSe2 grown via metal-organic chemical vapor deposition. <i>ACS Nano</i> , 2015 , 9, 2080-7	16.7	273
191	The influence of buffer layer coalescence on stress evolution in GaN grown on ion implanted AlN/Si(111) substrates. <i>Journal of Crystal Growth</i> , 2014 , 393, 98-102	1.6	5
190	Study of wafer thickness scaling in n-type rear-emitter solar cells with different bulk lifetimes. <i>Journal of Applied Physics</i> , 2014 , 116, 053105	2.5	

189	Molecular Doping Control at a Topological Insulator Surface: F4-TCNQ on Bi ₂ Se ₃ . <i>Journal of Physical Chemistry C</i> , 2014 , 118, 14860-14865	3.8	10
188	Ultrafast Electrical Measurements of Isolated Silicon Nanowires and Nanocrystals. <i>Journal of Physical Chemistry Letters</i> , 2014 , 5, 2050-7	6.4	18
187	Controlled growth of SiNPs by plasma synthesis. <i>Solar Energy Materials and Solar Cells</i> , 2014 , 124, 1-9	6.4	10
186	Ion-Implantation-Induced Damage Characteristics Within AlN and Si for GaN-on-Si Epitaxy. <i>Journal of Electronic Materials</i> , 2013 , 42, 833-837	1.9	1
185	Silicon nanowire growth on poly-silicon-on-quartz substrates formed by aluminum-induced crystallization. <i>Crystal Research and Technology</i> , 2013 , 48, n/a-n/a	1.3	1
184	Modification of dislocation behavior in GaN overgrown on engineered AlN film-on-bulk Si substrate. <i>Journal of Applied Physics</i> , 2013 , 113, 163108	2.5	3
183	GaN growth on Si pillar arrays by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2013 , 370, 259-264	1.6	1
182	Effect of AlN buffer layers on the surface morphology and structural properties of N-polar GaN films grown on vicinal C-face SiC substrates. <i>Journal of Crystal Growth</i> , 2013 , 377, 51-58	1.6	22
181	Vapor-liquid-solid growth of <110> silicon nanowire arrays 2013 ,		6
180	FDTD modeling of solar energy absorption in silicon branched nanowires. <i>Optics Express</i> , 2013 , 21 Suppl 3, A392-400	3.3	21
179	Effect of c-Si doping density on heterojunction with intrinsic thin layer (HIT) radial junction solar cells 2013 ,		2
178	Influence of growth stress on the surface morphology of N-polar GaN films grown on vicinal C-face SiC substrates. <i>Applied Physics Letters</i> , 2013 , 103, 241908	3.4	12
177	Metalorganic chemical vapor deposition of N-polar GaN films on vicinal SiC substrates using indium surfactants. <i>Applied Physics Letters</i> , 2012 , 100, 021913	3.4	27
176	Structural and electrical properties of epitaxial Bi ₂ Se ₃ thin films grown by hybrid physical-chemical vapor deposition. <i>Applied Physics Letters</i> , 2012 , 100, 162110	3.4	36
175	Epitaxial InGaN on nitridated Si(111) for photovoltaic applications 2012 ,		1
174	Dislocation bending and tensile stress generation in GaN and AlGaN films. <i>Journal of Crystal Growth</i> , 2012 , 359, 35-42	1.6	27
173	In Situ Stress Measurements During GaN Growth on Ion-Implanted AlN/Si Substrates. <i>Journal of Electronic Materials</i> , 2012 , 41, 865-872	1.9	5
172	Local electrode atom probe analysis of silicon nanowires grown with an aluminum catalyst. <i>Nanotechnology</i> , 2012 , 23, 215205	3.4	25

171	Tin-Catalyzed Plasma-Assisted Growth of Silicon Nanowires. <i>Journal of Physical Chemistry C</i> , 2011 , 115, 3833-3839	3.8	50
170	The effect of pattern density and wire diameter on the growth rate of micron diameter silicon wires. <i>Journal of Crystal Growth</i> , 2011 , 337, 1-6	1.6	13
169	$\text{MgB}_2/\text{MgO}/\text{MgB}_2$ Josephson Junctions for High-Speed Circuits. <i>IEEE Transactions on Applied Superconductivity</i> , 2011 , 21, 115-118	1.8	8
168	Seeding of silicon wire growth by out-diffused metal precipitates. <i>Small</i> , 2011 , 7, 563-7	11	3
167	Dual temperature process for reduction in regrowth interfacial charge in AlGaIn/GaN HEMTs grown on GaN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2053-2055		4
166	Single wire radial junction photovoltaic devices fabricated using aluminum catalyzed silicon nanowires. <i>Nanotechnology</i> , 2011 , 22, 445401	3.4	16
165	High-field properties of carbon-doped MgB_2 thin films by hybrid physical-chemical vapor deposition using different carbon sources. <i>Superconductor Science and Technology</i> , 2011 , 24, 125014	3.1	17
164	Gas phase equilibrium limitations on the vapor-liquid-solid growth of epitaxial silicon nanowires using SiCl_4 . <i>Journal of Materials Research</i> , 2011 , 26, 2207-2214	2.5	12
163	Ti/Al Ohmic Contacts to n-Type GaN Nanowires. <i>Journal of Nanomaterials</i> , 2011 , 2011, 1-6	3.2	1
162	High- J_c MgB_2 Josephson junctions with operating temperature up to 40 K. <i>Applied Physics Letters</i> , 2010 , 96, 042506	3.4	22
161	Nanoscale disorder in pure and doped MgB_2 thin films. <i>Superconductor Science and Technology</i> , 2010 , 23, 095008	3.1	12
160	Fabrication and characterization of axially doped silicon nanowire tunnel field-effect transistors. <i>Nano Letters</i> , 2010 , 10, 4813-8	11.5	67
159	Enhanced conversion efficiencies for pillar array solar cells fabricated from crystalline silicon with short minority carrier diffusion lengths. <i>Applied Physics Letters</i> , 2010 , 96, 213503	3.4	104
158	Radial junction silicon wire array solar cells fabricated by gold-catalyzed vapor-liquid-solid growth. <i>Applied Physics Letters</i> , 2010 , 97, 143108	3.4	81
157	Epitaxial regrowth of silicon for the fabrication of radial junction nanowire solar cells 2010 ,		4
156	Formation of nickel germanide contacts to Ge nanowires. <i>Applied Physics Letters</i> , 2010 , 97, 263116	3.4	27
155	Effect of indium surfactant on stress relaxation by V-defect formation in GaN epilayers grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2010 , 108, 093511	2.5	30
154	Surface morphology and thickness dependence of the properties of MgB_2 thin films by hybrid physical-chemical vapor deposition. <i>Superconductor Science and Technology</i> , 2010 , 23, 055004	3.1	20

153	Lithography-free synthesis of freestanding gold nanoparticle arrays encapsulated within dielectric nanowires 2010 ,		3
152	Effects of composition on dislocation microstructure and stress in Si-doped Al _x Ga _{1-x} N. <i>Journal of Crystal Growth</i> , 2010 , 312, 1301-1306	1.6	5
151	Growth and Characterization of Unintentionally Doped GaSb Nanowires. <i>Journal of Electronic Materials</i> , 2010 , 39, 355-364	1.9	31
150	Effect of reactor pressure on catalyst composition and growth of GaSb nanowires. <i>Journal of Crystal Growth</i> , 2010 , 312, 514-519	1.6	17
149	The nature of catalyst particles and growth mechanisms of GaN nanowires grown by Ni-assisted metal-organic chemical vapor deposition. <i>Nanotechnology</i> , 2009 , 20, 085610	3.4	41
148	Suppression of the vapor-liquid-solid growth of silicon nanowires by antimony addition. <i>Nanotechnology</i> , 2009 , 20, 025607	3.4	26
147	Thickness dependence of critical current density in MgB ₂ films fabricated by ex situ annealing of CVD-grown B films in Mg vapor. <i>Superconductor Science and Technology</i> , 2009 , 22, 015024	3.1	10
146	Growth Mechanisms and Size-Dependent Characteristics of Si and Si _{1-x} Ge _x Nanowires. <i>ECS Transactions</i> , 2009 , 25, 1145-1152	1	
145	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 2160-2164	2.9	33
144	Modeling studies of an impinging jet reactor design for hybrid physical-chemical vapor deposition of superconducting MgB ₂ films. <i>Journal of Crystal Growth</i> , 2009 , 311, 1501-1507	1.6	2
143	Growth and process modeling studies of nickel-catalyzed metalorganic chemical vapor deposition of GaN nanowires. <i>Journal of Crystal Growth</i> , 2009 , 311, 3409-3416	1.6	12
142	Fabrication and electrical properties of Si nanowires synthesized by Al catalyzed vapor-liquid-solid growth. <i>Nano Letters</i> , 2009 , 9, 4494-9	11.5	63
141	Tensile stress generation and dislocation reduction in Si-doped Al _x Ga _{1-x} N films. <i>Journal of Applied Physics</i> , 2009 , 106, 023506	2.5	37
140	Bottom-up assembly of large-area nanowire resonator arrays. <i>Nature Nanotechnology</i> , 2008 , 3, 88-92	28.7	257
139	Effect of polarity on the growth of InN films by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2008 , 104, 053112	2.5	16
138	In situ measurement of stress generation arising from dislocation inclination in Al _x Ga _{1-x} N:Si thin films. <i>Applied Physics Letters</i> , 2008 , 93, 111910	3.4	19
137	Prepassivation surface treatment effects on pulsed and dc I-V performance of AlGaIn/GaN high-electron-mobility transistors. <i>Applied Physics Letters</i> , 2008 , 92, 193505	3.4	5
136	Disorder dominated microwave conductance spectra of doped silicon nanowire arrays. <i>Nano Letters</i> , 2008 , 8, 1557-61	11.5	3

135	Raman Scattering from Si _{1-x} Ge _x Alloy Nanowires. <i>Journal of Physical Chemistry C</i> , 2008 , 112, 3209-3215	3.8	22
134	Properties of MgB ₂ films grown at various temperatures by hybrid physical-chemical vapour deposition. <i>Superconductor Science and Technology</i> , 2008 , 21, 095015	3.1	8
133	Diameter dependent growth rate and interfacial abruptness in vapor-liquid-solid Si/Si _{1-x} Ge _x heterostructure nanowires. <i>Nano Letters</i> , 2008 , 8, 1246-52	11.5	134
132	In situ axially doped n-channel silicon nanowire field-effect transistors. <i>Nano Letters</i> , 2008 , 8, 4359-64	11.5	34
131	High quality MgB ₂ thick films and large-area films fabricated by hybrid physical-chemical vapor deposition with a pocket heater. <i>Superconductor Science and Technology</i> , 2008 , 21, 085019	3.1	10
130	Clean epitaxial MgB ₂ films fabricated by the ex situ annealing of chemical vapour deposition-grown B films in Mg vapour. <i>Superconductor Science and Technology</i> , 2008 , 21, 045005	3.1	13
129	Oxidation of silicon nanowires for top-gated field effect transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008 , 26, 370-374	2.9	27
128	Nickel and nickel silicide Schottky barrier contacts to n-type silicon nanowires. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 1592		36
127	Growth of Thick MgB ₂ Films by Impinging-Jet Hybrid Physical-Chemical Vapor Deposition. <i>Advanced Materials</i> , 2008 , 20, 319-323	24	16
126	Effects of a compositionally graded buffer layer on stress evolution during GaN and Al _x Ga _{1-x} N MOCVD on SiC substrates. <i>Journal of Crystal Growth</i> , 2008 , 310, 2314-2319	1.6	10
125	Growth of thick p-type SiC epitaxial layers by halide chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2008 , 310, 4088-4093	1.6	24
124	Diameter-dependent composition of vapor-liquid-solid grown Si(1-x)Ge(x) nanowires. <i>Nano Letters</i> , 2007 , 7, 3241-5	11.5	51
123	Dual-Heater Reactor Design for Hybrid Physical-Chemical Vapor Deposition of MgB ₂ Thin Films. <i>IEEE Transactions on Applied Superconductivity</i> , 2007 , 17, 2862-2866	1.8	5
122	Selective plating for junction delineation in silicon nanowires. <i>Nano Letters</i> , 2007 , 7, 2642-4	11.5	4
121	Steady-state tensile stresses during the growth of polycrystalline films. <i>Acta Materialia</i> , 2007 , 55, 4973-4982	4.1	37
120	MgB ₂ thin films by hybrid physical-chemical vapor deposition. <i>Physica C: Superconductivity and Its Applications</i> , 2007 , 456, 22-37	1.3	98
119	Evolution of threading dislocations in MOCVD-grown GaN films on (111) Si substrates. <i>Journal of Crystal Growth</i> , 2007 , 300, 217-222	1.6	25
118	Modeling studies of the chemical vapor deposition of boron films from B ₂ H ₆ . <i>Journal of Crystal Growth</i> , 2007 , 299, 358-364	1.6	18

117	Silicon nanowire array photoelectrochemical cells. <i>Journal of the American Chemical Society</i> , 2007 , 129, 12344-5	16.4	204
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